

# Fangzhen Wu

## List of Publications by Year in descending order

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12  
papers

117  
citations

1651377

6  
h-index

1526636

10  
g-index

13  
all docs

13  
docs citations

13  
times ranked

109  
citing authors

#	ARTICLE	IF	CITATIONS
1	Direct Determination of Burgers Vectors of Threading Mixed Dislocations in 4H-SiC Grown by PVT Method. <i>Journal of Electronic Materials</i> , 2016, 45, 2045-2050.	1.0	15
2	Synchrotron X-ray topographic study on nature of threading mixed dislocations in 4H-SiC crystals grown by PVT method. <i>Journal of Crystal Growth</i> , 2016, 452, 39-43.	0.7	6
3	Characterization of V-shaped Defects in 4H-SiC Homoepitaxial Layers. <i>Journal of Electronic Materials</i> , 2015, 44, 1293-1299.	1.0	4
4	Direct Determination of Burgers Vectors of Threading Mixed Dislocations in 4H-SiC c-Plane Wafers Grown by PVT Method. <i>ECS Transactions</i> , 2015, 69, 33-38.	0.3	1
5	Direct Observation of Stacking Fault Nucleation from Deflected Threading Dislocations with Burgers Vector $c+a$ in PVT Grown 4H-SiC. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1693, 49.	0.1	3
6	A method to determine fault vectors in 4H-SiC from stacking sequences observed on high resolution transmission electron microscopy images. <i>Journal of Applied Physics</i> , 2014, 116, 104905.	1.1	2
7	Characterization of Threading Dislocations in PVT-Grown AlN Substrates via x-Ray Topography and Ray Tracing Simulation. <i>Journal of Electronic Materials</i> , 2014, 43, 838-842.	1.0	29
8	Characterization and Formation Mechanism of Six Pointed Star-Type Stacking Faults in 4H-SiC. <i>Journal of Electronic Materials</i> , 2013, 42, 787-793.	1.0	3
9	Quantitative Comparison Between Dislocation Densities in Offcut 4H-SiC Wafers Measured Using Synchrotron X-ray Topography and Molten KOH Etching. <i>Journal of Electronic Materials</i> , 2013, 42, 794-798.	1.0	5
10	Grazing Incidence X-ray Topographic Studies of Threading Dislocations in Hydrothermal Grown ZnO Single Crystal Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2013, 1494, 121-126.	0.1	7
11	Simulation of Grazing-Incidence Synchrotron X-ray Topographic Images of Threading $c+a$ Dislocations in 4H-SiC. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1433, 53.	0.1	23
12	Analysis of Dislocation Behavior in Low Dislocation Density, PVT-Grown, Four-Inch Silicon Carbide Single Crystals. <i>Materials Research Society Symposia Proceedings</i> , 2010, 1246, 1.	0.1	18